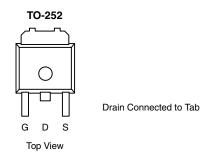


SUD50N02-06P N-Channel

20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a			
20	0.0060 at V _{GS} = 10 V	26			
20	0.0095 at V _{GS} = 4.5 V	21			



Ordering Information: SUD50N02-06P-E3 (Lead (Pb) free)

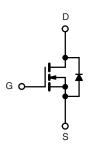
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized for High Efficiency
- 100 % R_q Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

APPLICATIONS

- Synchronous Buck DC/DC Conversion
 - Desktop
 - Server



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20	V		
Gate-Source Voltage		V _{GS}	± 20	V		
Outline Paris Outline	T _A = 25 °C	I-	26 ^a			
Continuous Drain Current ^a	T _C = 25 °C	I _D	50 ^b			
Pulsed Drain Current		I _{DM}	100	Α		
Continuous Source Current (Diode Conduction) ^a		I _S	26			
Avalanche Current	L = 0.1 mH	I _{AS}	45			
Single Pulse Avalanche Energy	L = 0.1 IIII1	E _{AS}	101	mJ		
Maximum Power Dissipation	T _A = 25 °C	P _D	6.8 ^a	W		
Maximum Fower Dissipation	T _C = 25 °C] 'D [65] "		
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifesture Ituration to Ameliant	t ≤ 10 s	- R _{thJA}	18	22	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		40	50		
Maximum Junction-to-Case		R _{thJC}	1.9	2.3		

Notes:

- a. Surface mounted on FR4 board, $t \le 10$ s.
- b. Limited by package.



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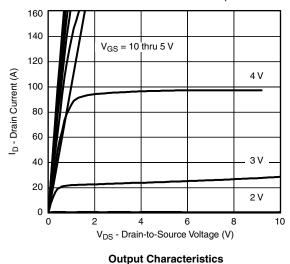
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l L		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
Gate Threshold Voltage	V _{GS(th)}				3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1 μA		
Zero date voltage Brain Garrent	.055	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50	μΑ	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
		$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$		0.0046	0.006		
Drain-Source On-State Resistance ^b	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125 \text{ °C}$			0.0084	Ω	
		$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0073	0.0095		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$	15			S	
Dynamic ^a							
Input Capacitance	C _{iss}			2550		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$		900			
Reverse Transfer Capacitance	C _{rss}			415			
Total Gate Charge ^c	Q_g			19	30		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$		7.5		nC	
Gate-Drain Charge ^c	Q _{gd}			6			
Gate Resistance	R_g		0.5	1.5	2.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			11	20		
Rise Time ^c	t _r	$V_{DD} = 10 \text{ V}, R_{L} = 0.2 \Omega$		10	15	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		24	35	115	
Fall Time ^c	t _f			9	15		
Source-Drain Diode Ratings and Cha	racteristic (T	C = 25 °C)					
Pulsed Current	I _{SM}				100	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, dl/dt = 100 A/μs		35	70	ns	

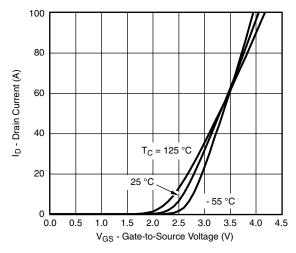
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C unless noted)





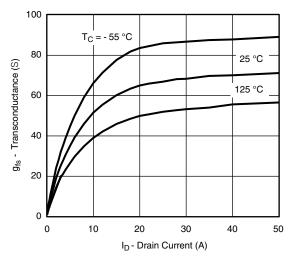
Transfer Characteristics



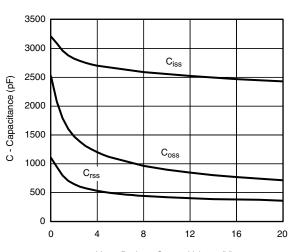
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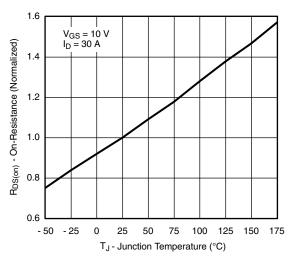
TYPICAL CHARACTERISTICS (25 °C unless noted)



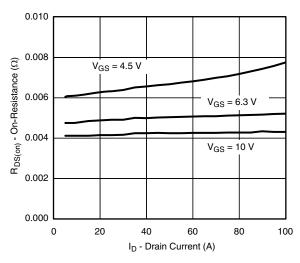
Transconductance



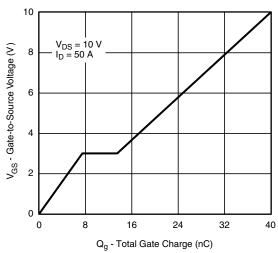
 V_{DS} - Drain-to-Source Voltage (V) $\label{eq:capacitance}$



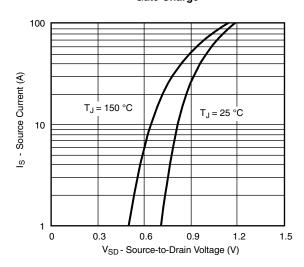
On-Resistance vs. Junction Temperature



On-Resistance vs. Drain Current



Gate Charge

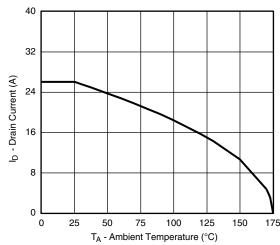


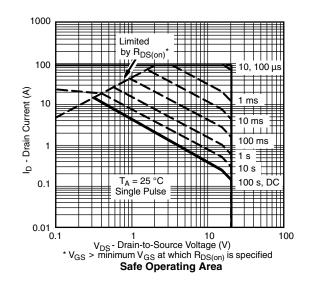
Source-Drain Diode Forward Voltage

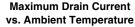
SUD50N02-06P

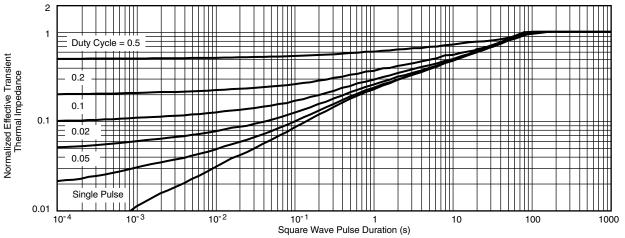
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THERMAL RATINGS

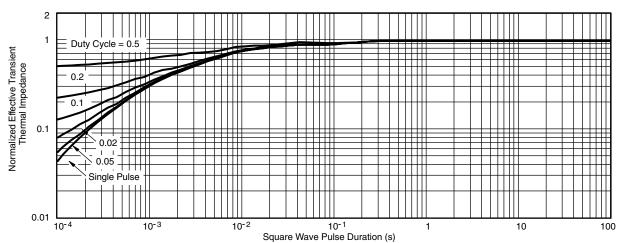










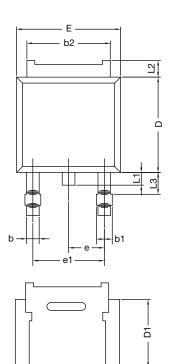


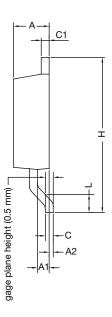
Normalized Thermal Transient Impedance, Junction-to-Case

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TO-252AA CASE OUTLINE





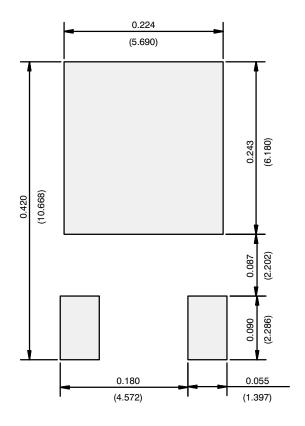
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090	BSC	
e1	4.57	BSC	0.180	BSC	
Η	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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